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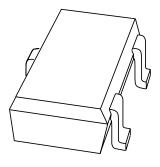
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Kind regards,

Team Nexperia

# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BFS20W**NPN medium frequency transistor

Product data sheet 1999 Apr 21



# NPN medium frequency transistor

BFS20W

#### **FEATURES**

- Low current (max. 25 mA)
- Low voltage (max. 20 V).
- Very low feedback capacitance (typ. 350 fF).

#### **APPLICATIONS**

• IF and VHF applications in thick and thin-film circuits.

#### **DESCRIPTION**

NPN medium frequency transistor in a SOT323 (SC-70) plastic package.

#### **MARKING**

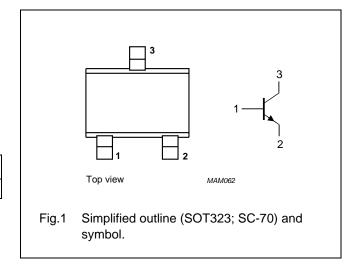
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BFS20W	N1*

#### Note

- 1. \* = -: Made in Hong Kong.
  - \* = t: Made in Malaysia.

#### **PINNING**

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	30	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	20	V
$V_{EBO}$	emitter-base voltage	open collector	_	4	٧
I <sub>C</sub>	collector current (DC)		_	25	mA
I <sub>CM</sub>	peak collector current		_	25	mA
I <sub>BM</sub>	peak base current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

# NPN medium frequency transistor

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	625	K/W

#### Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

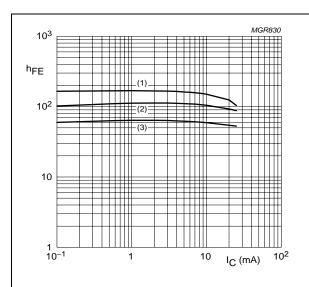
#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V	_	_	100	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V; T <sub>j</sub> = 100 °C	-	_	10	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 4 V	-	_	100	nA
h <sub>FE</sub>	DC current gain	$I_C = 7 \text{ mA}; V_{CE} = 10 \text{ V}$	40	85	_	
$V_{BE}$	base-emitter voltage	$I_C = 7 \text{ mA}; V_{CE} = 10 \text{ V}$	-	740	900	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	-	1	_	pF
C <sub>re</sub>	feedback capacitance	I <sub>C</sub> = 0; V <sub>CE</sub> = 10 V; f = 1 MHz	-	350	_	fF
f <sub>T</sub>	transition frequency	$I_C = 5 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	360	470	_	MHz

# NPN medium frequency transistor

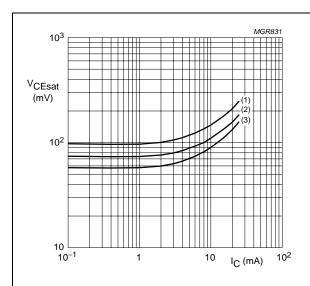
BFS20W



 $V_{CE} = 10 \text{ V}.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

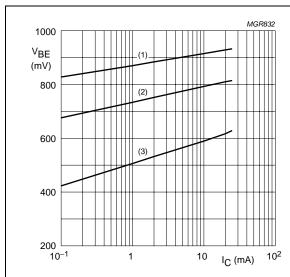
Fig.2 DC current gain as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10$ .

- (1)  $T_{amb} = 100 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

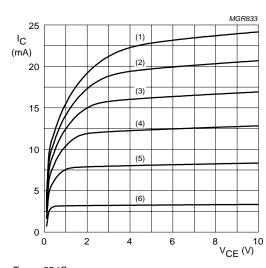
Fig.3 Collector-emitter saturation voltage as a function of collector current; typical values.



 $V_{CE} = 10 \text{ V}.$ 

- (1)  $T_{amb} = -100 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.4 Base-emitter voltage as a function of collector current; typical values.



 $T_{amb} = 25 \, ^{\circ}C.$ 

- (1)  $I_B = 280 \mu A$ .
- (4)  $I_B = 130 \mu A$ .
- (2)  $I_B = 230 \mu A$ .
- (5)  $I_B = 80 \mu A$ .
- (3)  $I_B = 180 \mu A$ .
- (6)  $I_B = 30 \mu A$ .

rig.5 Collector current as a function of collector-emitter voltage; typical values.

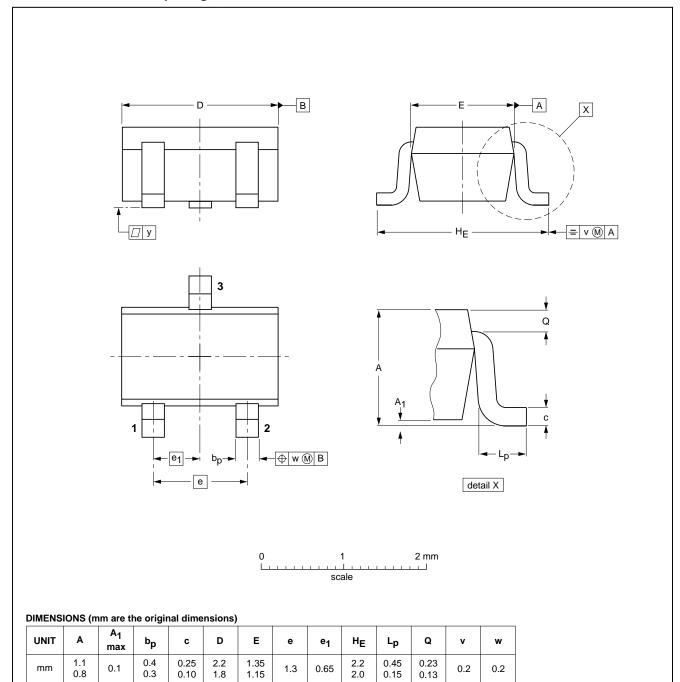
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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

**SOT323** 



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT323			SC-70			97-02-28

# NPN medium frequency transistor

BFS20W

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com

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 Printed in The Netherlands
 115002/00/01/pp7
 Date of release: 1999 Apr 21
 Document order number: 9397 750 05696



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